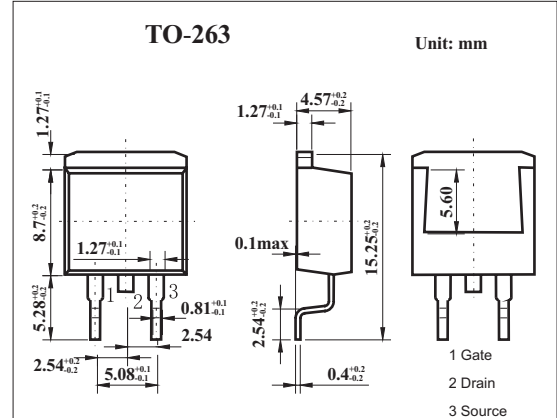
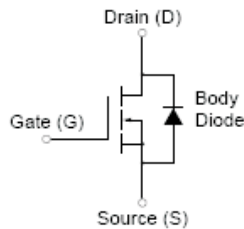


■ Features

- Low gate charge  
 $Q_G = 26 \text{ nC TYP. (} I_D = 7.5 \text{ A, } V_{DD} = 450 \text{ V, } V_{GS} = 10 \text{ V)}$
- Gate voltage rating  $\pm 30 \text{ V}$
- Low on-state resistance  
 $R_{DS(on)} = 1.2 \ \Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 3.75 \text{ A)}$
- Avalanche capability ratings



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	$V_{DSS}$	600	V
Gate to source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	$I_D$	$\pm 7.5$	A
	$I_{DP}^*$	$\pm 30$	A
Power dissipation	$P_D$	$T_A=25^\circ\text{C}$	1.5
		$T_C=25^\circ\text{C}$	70
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\*  $PW \leq 10 \ \mu\text{s, Duty Cycle} \leq 1\%$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	$I_{DSS}$	$V_{DS}=600\text{V, } V_{GS}=0$			100	$\mu\text{A}$
Gate leakage current	$I_{GSS}$	$V_{GS}=\pm 30\text{V, } V_{DS}=0$			$\pm 100$	$\mu\text{A}$
Gate to source cut off voltage	$V_{GS(off)}$	$V_{DS}=10\text{V, } I_D=1\text{mA}$	2.5		3.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10\text{V, } I_D=3.75\text{A}$	2.0			S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V, } I_D=3.75\text{A}$		0.9	1.2	$\Omega$
Input capacitance	$C_{iss}$	$V_{DS}=10\text{V, } V_{GS}=0, f=1\text{MHZ}$		1100		pF
Output capacitance	$C_{oss}$		200			pF
Reverse transfer capacitance	$C_{rss}$		20			pF
Turn-on delay time	$t_{on}$	$I_D=3.75\text{A, } V_{GS(on)}=10\text{V, } V_{DD}=150\text{V, } R_G=10\ \Omega, R_L=50\ \Omega$		18		ns
Rise time	$t_r$		15			ns
Turn-off delay time	$t_{off}$		50			ns
Fall time	$t_f$		15			ns